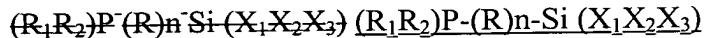


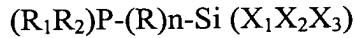
IN THE CLAIMS

1. (Currently Amended) A material for forming copper undercoat films, ~~characterized by~~ comprising [[the]] a compound represented by the general formula (1) ~~below~~:

General formula (1)

~~(In general formula 1, wherein~~ at least one of X_1 , X_2 and X_3 is a hydrolytic group, R_1 and R_2 are alkyl groups, R denotes a chain-form organic group formed from alkyl groups, aromatic rings or alkyl groups containing aromatic rings, and n is an integer from 1 to 6. [D])

2. (Currently Amended) A material for forming copper undercoat films, ~~characterized by~~ comprising a compound represented by the general formula (1) ~~below~~:

General formula (1)

~~(In general formula 1, wherein~~ at least one of X_1 , X_2 and X_3 is selected from a group comprising halogens, alkoxide groups, amino groups and isocyanate groups, R_1 and R_2 are alkyl groups with carbon numbers of 1-21, R has a carbon number of 1-50, and denotes a chain-form organic group formed from alkyl groups, aromatic rings or alkyl groups containing aromatic rings, and n is an integer from 1 to 6. [D])

3. (Currently Amended) The material for forming copper undercoat films according to claim 1 ~~or 2~~, characterized by ~~being a material for forming copper undercoat films by virtue of~~ the bonding of $(R_1R_2)P-(R)n-Si$ groups to a substrate via Si-O bonding, and by ~~comprising a solvent and by~~ the compound represented by the general formula [[(1)]].

4. (Currently Amended) The material for forming copper undercoat films according to claim 1, any of claims 1-3, characterized in that the compound represented by the general formula [(I)] is ~~one or more substances~~ selected from the group~~[:]~~ consisting of: 1-dimethylphosphino-2-triethoxysilylthane, 1-diethylphosphino-2-triethoxysilylthane, 1-diphenylphosphino-2-triethoxysilylthane, 1-dimethylphosphino-2-trimethoxysilylthane, 1-diethylphosphino-2trimethoxysilylthane, 1-diphenylphosphino-2-trimethoxysilylthane, 1-dimethylphosphino-3triethoxysilylpropane, 1-diethylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-2-trichlorosilylthane, 1-diphenylphosphino-2trisdimethylaminosilylthane, 1-diphenylphosphino-2-triisocyanatosilylthane and 1-diphenylphosphino-4-triethoxysilylethylbenzene.

5. (Currently Amended) The material for forming copper undercoat films according to claim 1, any of claims 1-4, characterized in that the material for forming copper undercoat films is brought into contact with a substrate surface, thus forming a copper undercoat film.

6. (Currently Amended) The material for forming copper undercoat films according to claim 5, any of claims 1-5, wherein the undercoat film is produced by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein said undercoat film is [designed so that] the reaction between [[the]] -Si(X₁X₂X₃) groups and -OH groups at the substrate surface occurs in liquid phase.

7. (Currently Amended) The material for forming copper undercoat films according to claim 5, any of claims 1-5, wherein the undercoat film is produced by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein said undercoat film is [designed so that] the reaction between [[the]] -Si (X₁X₂X₃) groups and -OH groups at the substrate surface occurs in gas phase.

8. (Currently Amended) The material for forming copper undercoat films according to ~~any~~ ~~of claims 1-5, claim 5,~~ wherein the undercoat film is produced by the bonding of $(R_1R_2)-(R)_n-Si$ groups to the substrate via Si-O bonding, and ~~wherein said undercoat film is [designed so that]~~ the reaction between [[the]] $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in a supercritical liquid.

9. (Currently Amended) The material for forming copper undercoat films according to ~~any~~ ~~of claims 1-8, claim 5,~~ characterized in that the reaction between [[the]] $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface is carried out under the condition of room temperature to 450 °C.

10. (New) The material for forming copper undercoat films according to claim 2, characterized by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to a substrate via Si-O bonding, by a solvent and by the compound represented by the general formula.

11. (New) The material for forming copper undercoat films according to claim 2, characterized in that the compound represented by the general formula is selected from the group consisting of: 1-dimethylphosphino-2-triethoxysilylethane, 1-diethylphosphino-2-triethoxysilylethane, 1-diphenylphosphino-2-triethoxysilylethane, 1-dimethylphosphino-2-trimethoxysilylethane, 1-diethylphosphino-2trimethoxysilylethane, 1-diphenylphosphino-2-trimethoxysilylethane, 1-dimethylphosphino-3triethoxysilylpropane, 1-diethylphosphino-3-trimethoxysilylethane, 1-diphenylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-2-trichlorosilylethane, 1-diphenylphosphino-2trisdimethylaminosilylethane, 1-diphenylphosphino-2-triisocyanatosilylethane and 1-diphenylphosphino-4-triethoxysilylethylbenzene.

12. (New) The material for forming copper undercoat films according to claim 2, characterized in that the material for forming copper undercoat films is brought into contact with a substrate surface, thus forming a copper undercoat film.

13. (New) The material for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in liquid phase.

14. (New) The material for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of $(R_1R_2)P-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in gas phase.

15. (New) The material for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of $(R_1R_2)-(R)_n-Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in a supercritical liquid.

16. (New) The material for forming copper undercoat films according to claim 12, characterized in that the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface is carried out under the condition of room temperature to 450 °C.